

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC2500

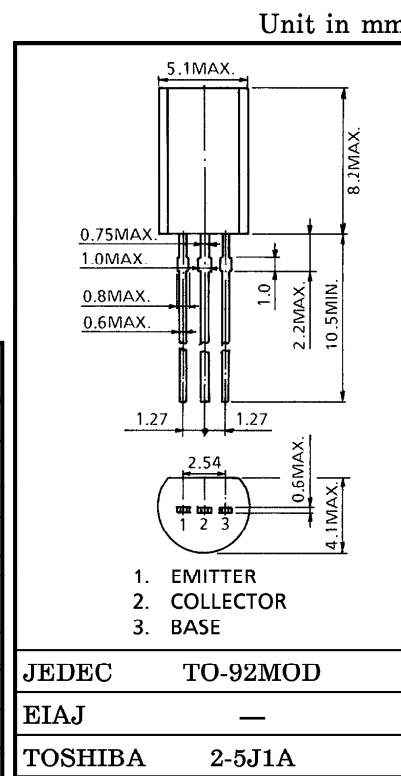
STROBE FLASH APPLICATIONS.

MEDIUM POWER AMPLIFIER APPLICATIONS.

- High DC Current Gain and Excellent h_{FE} Linearity
 - : $h_{FE}(1) = 140 \sim 600$ ($V_{CE} = 1V$, $I_C = 0.5A$)
 - : $h_{FE}(2) = 70$ (Min.), 200 (Typ.) ($V_{CE} = 1V$, $I_C = 2A$)
- Low Saturation Voltage
 - : $V_{CE(sat)} = 0.5V$ (Max.) ($I_C = 2A$, $I_B = 50mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	30	V
Collector-Emitter Voltage		V_{CES}	30	V
		V_{CEO}	10	
Emitter-Base Voltage		V_{EBO}	6	V
Collector Current	DC	I_C	2	A
	Pulsed (Note 1)	I_{CP}	5	
Base Current		I_B	0.5	A
Collector Power Dissipation		P_C	900	mW
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$

Note 1 : Pulse Width $\leq 10ms$, Duty Cycle $\leq 30\%$ 

Weight : 0.36g

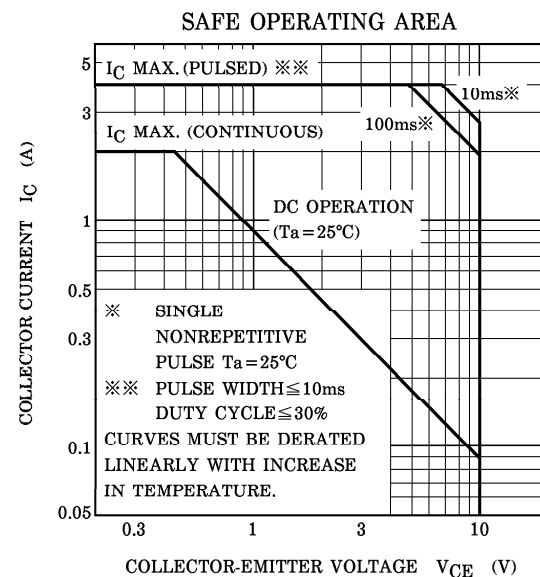
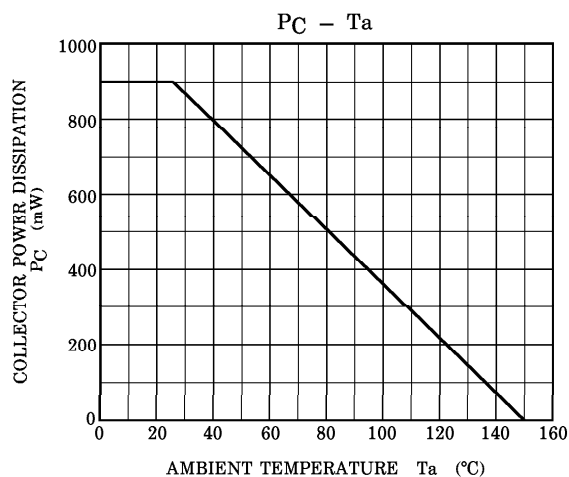
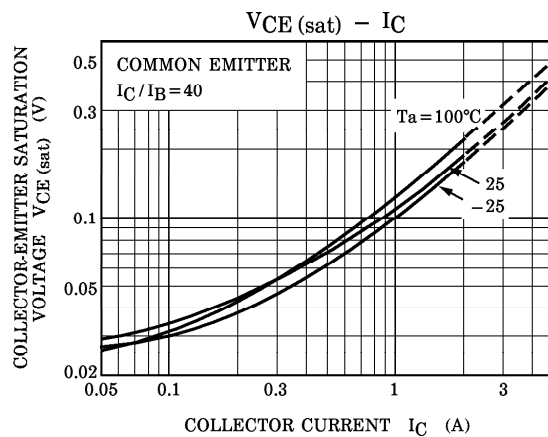
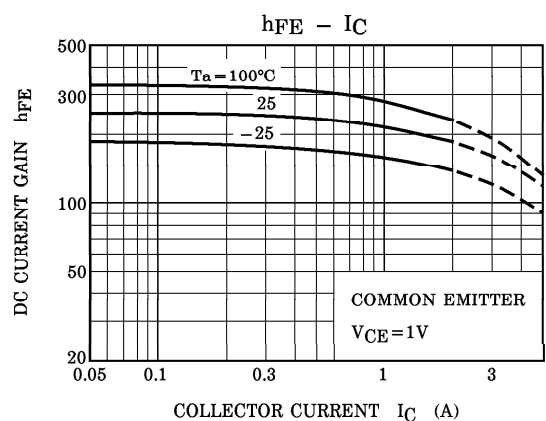
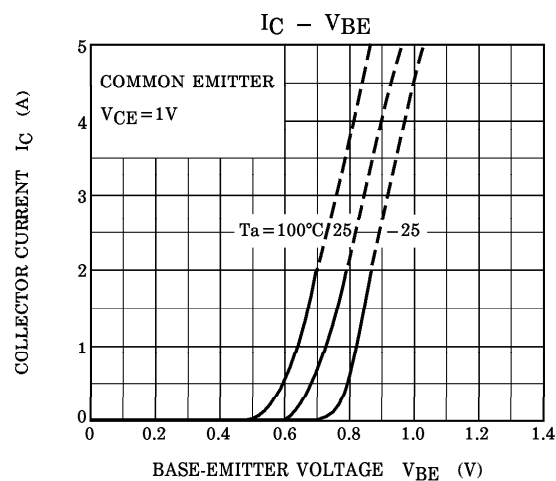
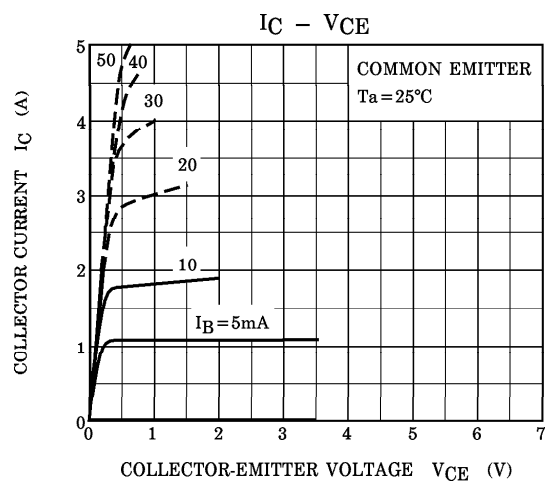
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 30V$, $I_E = 0$	—	—	100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 6V$, $I_C = 0$	—	—	100	nA
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C = 10mA$, $I_B = 0$	10	—	—	V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E = 1mA$, $I_C = 0$	6	—	—	V
DC Current Gain	$h_{FE}(1)$ (Note 2)	$V_{CE} = 1V$, $I_C = 0.5A$	140	—	600	
	$h_{FE}(2)$	$V_{CE} = 1V$, $I_C = 2A$	70	200	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2A$, $I_B = 50mA$	—	0.2	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 1V$, $I_C = 2A$	—	0.86	1.5	V
Transition Frequency	f_T	$V_{CE} = 1V$, $I_C = 0.5A$	—	150	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V$, $I_E = 0$, $f = 1MHz$	—	27	—	pF

Note 2 : $h_{FE}(1)$ Classification A : 140~240, B : 200~330, C : 300~450, D : 420~600

961001EAA2

● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.



961001EAA2'

- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.